

14 a second interconnect selectively provided on the second interlayer
15 insulating film and electrically connected to the first interconnect through a
16 second contact hole formed in the second interlayer insulating film; and
17
18 a passivation layer provided so as to cover the second interconnect.

Please add the following new claim 28:

1 28. (Newly Added) A semiconductor device, comprising:
2 a capacitor provided on a supporting substrate having an integrated
3 circuit thereon and including a lower electrode, a dielectric film, and an upper
4 electrode;
5 a first interlayer insulating film provided so as to cover the
6 capacitor;
7 a first interconnect selectively provided on the first interlayer
8 insulating film and electrically connected to the integrated circuit and the
9 capacitor through a first contact hole formed in the first interlayer insulating
10 film;
11 a second interlayer insulating film provided so as to cover the first
12 interconnect;
13 a hydrogen supplying layer provided between the first interconnect
14 and the second interlayer insulating film excluding an area in which the capacitor
15 is provided, said hydrogen supplying layer having a sufficient amount of
16 hydrogen for repairing damage done to the integrated circuit caused in forming
17 the first contact hole;
18 a second interconnect selectively provided on the second interlayer
19 insulating film and electrically connected to the first interconnect through a
20 second contact hole formed in the second interlayer insulating film; and
21 a passivation layer provided so as to cover the second interconnect.